

AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Previously Presented) A thin film transistor comprising:
an insulating layer having a first opening;
a first conductive layer fitted in the first opening; and
a second conductive layer on and in contact with the insulating layer and the first conductive layer,
wherein the first conductive layer is thicker than the second conductive layer in a vertical direction, and
wherein a surface of the insulating layer and the first conductive layer is planarized and a uniform surface.
2. (Previously Presented) A thin film transistor comprising:
an insulating layer having a first opening;
a first conductive layer fitted in the first opening; and
a second conductive layer on and in contact with the insulating layer and the first conductive layer,
wherein the first conductive layer is thicker than the second conductive layer in a vertical direction,
wherein a surface of the insulating layer and the first conductive layer is planarized and a uniform surface, and
wherein the second conductive layer is formed by a droplet discharge method using a conductive material.
3. (Previously Presented) A display device comprising:
a first insulating layer having a first opening;
a first conductive layer fitted in the first opening;
a second conductive layer on and in contact with the first insulating layer and the first conductive layer;
a semiconductor layer over the second conductive layer with a gate insulating film therebetween;
a third conductive layer over the semiconductor layer;

a second insulating layer having a second opening over the third conductive layer; and
a fourth conductive layer fitted in the second opening,
wherein the first conductive layer is thicker than the second conductive layer in a
vertical direction,

wherein a surface of the first insulating layer and the first conductive layer is
planarized and a uniform surface, and

wherein the fourth conductive layer is thicker than the third conductive layer.

4. (Previously Presented) A display device comprising:

a first insulating layer having a first opening;

a first conductive layer fitted in the first opening;

a second conductive layer on and in contact with the first insulating layer and the first
conductive layer;

a semiconductor layer over the second conductive layer with a gate insulting film
therebetween;

a third conductive layer over the semiconductor layer;

a second insulating layer having a second opening over the third conductive layer; and

a fourth conductive layer fitted in the second opening,

wherein the first conductive layer is thicker than the second conductive layer in a
vertical direction,

wherein a surface of the first insulating layer and the first conductive layer is
planarized and a uniform surface,

wherein the fourth conductive layer is thicker than the third conductive layer, and

wherein each of the second conductive layer and the third conductive layer is formed
by a droplet discharge method using a conductive material.

5. (Previously Presented) A display device comprising:

a first insulating layer having a first opening;

a first conductive layer fitted in the first opening;

a second conductive layer on and in contact with the first insulating layer and the first
conductive layer;

a semiconductor layer over the second conductive layer with a gate insulting film
therebetween;

a pair of third conductive layers over the semiconductor layer;
a first electrode over one of the pair of third conductive layers;
an electroluminescent layer over the first electrode; and
a second electrode over the electroluminescent layer,
wherein the first conductive layer is thicker than the second conductive layer in a vertical direction, and
wherein a surface of the first insulating layer and the first conductive layer is planarized and a uniform surface.

6. (Previously Presented) A display device comprising
a first insulating layer having a first opening;
a first conductive layer fitted in the first opening;
a second conductive layer on and in contact with the first insulating layer and the first conductive layer;
a semiconductor layer over the second conductive layer with a gate insulating film therebetween;
a pair of third conductive layers over the semiconductor layer;
a first electrode over one of the pair of third conductive layers;
an electroluminescent layer over the first electrode; and
a second electrode over the electroluminescent layer,
wherein the first conductive layer is thicker than the second conductive layer in a vertical direction,
wherein a surface of the first insulating layer and the first conductive layer is planarized and a uniform surface, and
wherein the second conductive layer is formed by a droplet discharge method using a conductive material.

7. (Previously Presented) A display device comprising:
a first insulating layer having a first opening;
a first conductive layer fitted in the first opening;
a second conductive layer on and in contact with the insulating layer and the first conductive layer;

a semiconductor layer over the second conductive layer with a gate insulating film therebetween;

a pair of third conductive layers over the semiconductor layer;

a first electrode over one of the pair of third conductive layers;

a second insulating layer having a second opening over the other one of the pair of third conductive layers;

a fourth conductive layer fitted in the second opening;

an electroluminescent layer over the first electrode; and

a second electrode over the electroluminescent layer,

wherein the first conductive layer is thicker than the second conductive layer in a vertical direction,

wherein a surface of the first insulating layer and the first conductive layer is planarized and a uniform surface, and

wherein the fourth conductive layer is thicker than the pair of third conductor layers.

8. (Previously Presented) A display device comprising:

a first insulating layer having a first opening;

a first conductive layer fitted in the first opening;

a second conductive layer on and in contact with the first insulating layer and the first conductive layer;

a semiconductor layer over the second conductive layer with a gate insulating film therebetween;

a pair of third conductive layers over the semiconductor layer;

a first electrode over one of the pair of third conductive layers;

a second insulating layer having a second opening over the other one of the pair of third conductive layers;

a fourth conductive layer fitted in the second opening;

an electroluminescent layer over the first electrode; and

a second electrode over the electroluminescent layer,

wherein the first conductive layer is thicker than the second conductive layer in a vertical direction,

wherein a surface of the first insulating layer and the first conductive layer is planarized and a uniform surface,

wherein the fourth conductive layer is thicker than the pair of third conductive layers,
and

wherein each of the second conductive layer and the third conductive layer is formed
by a droplet discharge method using a conductive material.

9. (Original) The thin film transistor or the display device according to any one of
claims 1 to 8, wherein the thin film transistor or the display device further comprises a
titanium oxide film below the first conductive layer.

10. (Original) The thin film transistor or the display device according to any one of
claims 1 to 8, wherein the thin film transistor or the display device further comprises a film
comprising at least one selected from the group consisting of W (tungsten), Al (aluminum),
Ta (tantalum), Zr (zirconium), Hf (hafnium), Ir (iridium), Nb (niobium), Pd (lead), Pt
(platinum), Mo (molybdenum), Rh (rhodium), Sc (scandium), Ti (titanium), V (vanadium),
Cr (chromium), Mn (manganese), Fe (iron), Co (cobalt), Ni (nickel), Cu (copper), and Zn
(zinc) below the first conductive layer.

11. (Original) The thin film transistor or the display device according to any one of
claims 1 to 8, wherein the second conductive layer includes at least one of silver, gold,
copper, and indium tin oxide.

12. (Original) The display device according to any one of claims 3 to 8, wherein the third
conductive layer includes at least one of silver, gold, copper, and indium tin oxide.

13. (Original) The thin film transistor or the display device according to any one of
claims 1 to 8, wherein a width of the first opening is from 5 μm to 100 μm .

14. (Original) The display device according to any one of claims 3 to 8, wherein the
semiconductor layer is an amorphous semiconductor layer including at least one of hydrogen
and halogen.

15. (Previously Presented) The display device according to any one of claims 3 to 8, wherein the semiconductor layer is a semi-amorphous semiconductor layer including at least one of hydrogen and halogen.

16. (Original) The display device according to any one of claims 3 to 8, wherein the semiconductor layer is a polycrystalline semiconductor including at least one of hydrogen and halogen.

17. (Original) The display device according to any one of claims 3 to 8, wherein a channel length of the semiconductor layer is from 5 μm to 100 μm .

18. (Original) A television apparatus including the display device according to any one of claims 3 to 8 as a display screen.

19. (Original) A television apparatus including a display device with the thin film transistor according to claims 1 or 2 as a display screen.

20.-32. (Canceled)

33. (New) The display device according to claim 1 or 2, wherein the insulating layer is formed by using an inorganic insulating material, a heat-resistant high molecular weight material, inorganic siloxane or an organosiloxane-based insulating material.

34. (New) The display device according to any one of claim 3 to 8, wherein the first insulating layer is formed by using an inorganic insulating material, a heat-resistant high molecular weight material, inorganic siloxane or an organosiloxane-based insulating material.

35. (New) The display device according to any one of claim 3, 4, 7 and 8, wherein the second insulating layer is formed by using an inorganic insulating material, a heat-resistant high molecular weight material, inorganic siloxane or an organosiloxane-based insulating material.